

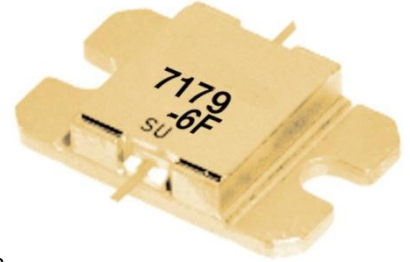
FEATURES

- High Output Power: $P_{1dB} = 38.5\text{dBm}$ (Typ.)
- High Gain: $G_{1dB} = 9.0\text{dB}$ (Typ.)
- High PAE: $\eta_{add} = 34\%$ (Typ.)
- Low IM3 = $-46\text{dBc}@P_o = 27.5\text{dBm}$
- Broad Band: 7.1 to 7.9GHz
- Impedance Matched $Z_{in}/Z_{out} = 50\text{ohm}$
- Hermetically Sealed Package

DESCRIPTION

The FLM7179-6F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50 ohm system.

SEDI's stringent Quality Assurance Program assures the highest reliability and consistent performance.



ABSOLUTE MAXIMUM RATING (Case Temperature $T_c=25\text{deg.C}$)

Item	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}		15	V
Gate-Source Voltage	V_{GS}		-5	V
Total Power Dissipation	P_T	$T_c = 25\text{deg.C}$	37.5	W
Storage Temperature	T_{stg}		-65 to +175	deg.C
Channel Temperature	T_{ch}		175	deg.C

SEDI recommends the following conditions for the reliable operation of GaAs FETs:

1. The drain-source operating voltage (V_{DS}) should not exceed 10 volts.
2. The forward and reverse gate currents should not exceed 16.0 and -2.8 mA respectively with gate resistance of 100ohm.

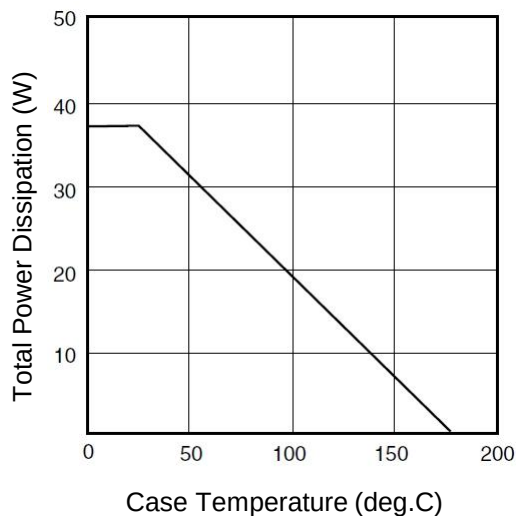
ELECTRICAL CHARACTERISTICS (Case Temperature $T_c=25\text{deg.C}$)

Item	Symbol	Test Conditions	Limit			Unit
			Min.	Typ.	Max.	
Saturated Drain Current	I_{DSS}	$V_{DS}=5V, V_{GS}=0V$	-	2500	3750	mA
Transconductance	g_m	$V_{DS}=5V, I_{DS}=1625\text{mA}$	-	2500	-	mS
Pinch-off Voltage	V_p	$V_{DS}=5V, I_{DS}=125\text{mA}$	-0.5	-1.5	-3.0	V
Gate Source Breakdown Voltage	V_{GSO}	$I_{GS}=-125\text{uA}$	-5.0	-	-	V
Output Power at 1dB G.C.P.	P_{1dB}	$V_{DS}=10V,$ $I_{DS}=0.65 I_{DSS}$ (Typ.), $f=7.1$ to 7.9 GHz, $Z_S=Z_L=50\text{ohm}$	37.5	38.5	-	dBm
Power Gain at 1dB G.C.P.	G_{1dB}		8.0	9.0	-	dB
Drain Current	I_{DSR}		-	1625	2000	mA
Power-added Efficiency	η_{add}		-	34	-	%
Gain Flatness	ΔG		-	-	1.2	dB
3rd Order Intermodulation Distortion	IM_3	$f = 7.9$ GHz, $\Delta f = 10$ MHz 2-Tone Test $P_{out} = 27.5\text{dBm}$ S.C.L.	-44	-46	-	dBc
Thermal Resistance	R_{th}	Channel to Case	-	3.0	4.0	deg.C/W
Channel Temperature Rise	ΔT_{ch}	$10V \times I_{DSR} \times R_{th}$	-	-	80	deg.C

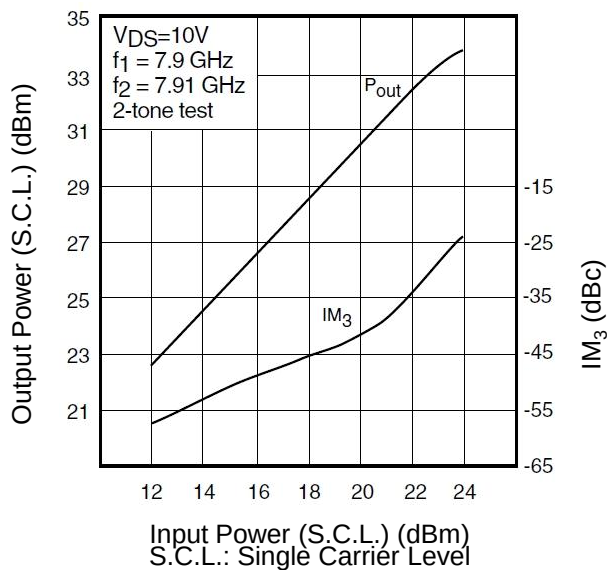
G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

CASE STYLE	IB	
ESD	Class 3A	4000V to 8000V
Note : Based on JEDEC JESD22-A114 (C=100pF, R=1.5kohm)		
RoHS Compliance	Yes	

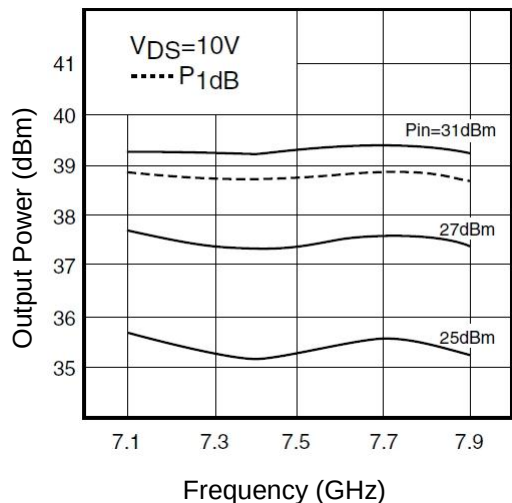
POWER DERATING CURVE



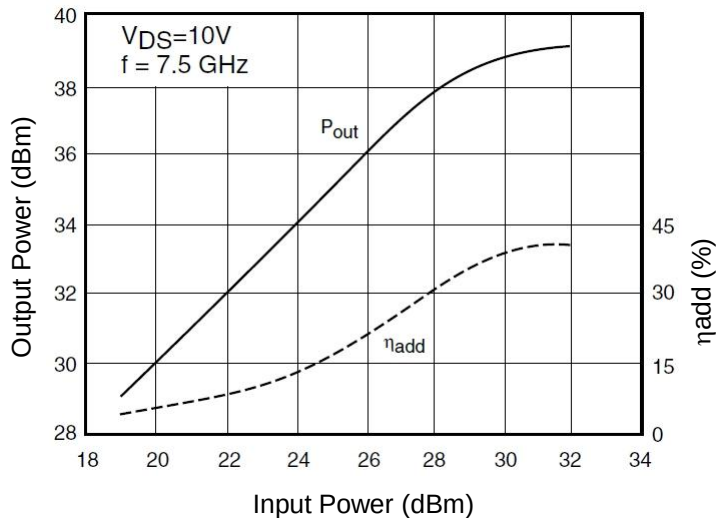
OUTPUT POWER & IM₃ vs. INPUT POWER

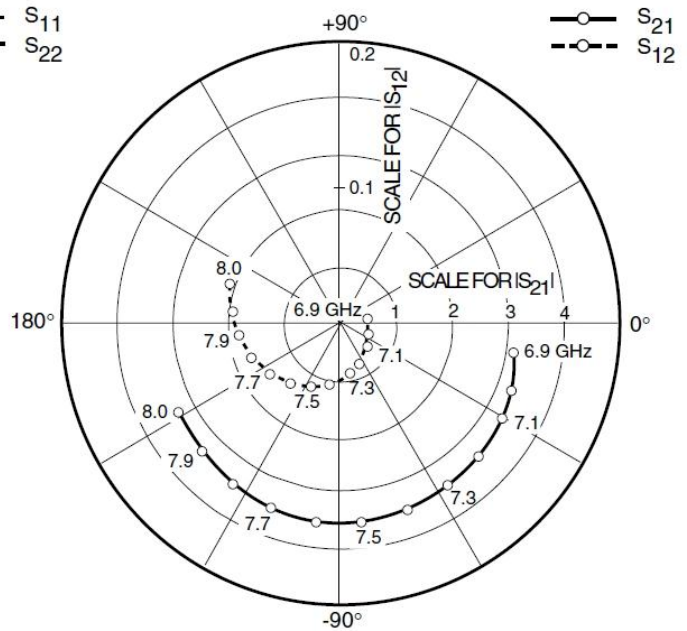
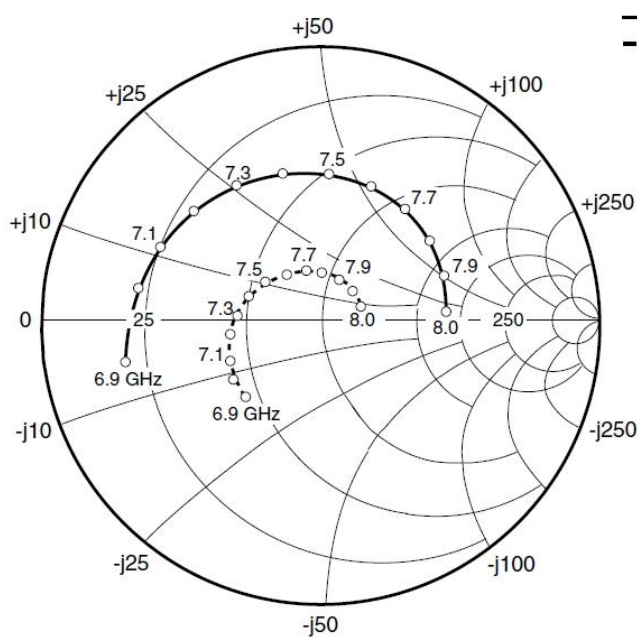


OUTPUT POWER vs. FREQUENCY



OUTPUT POWER vs. INPUT POWER



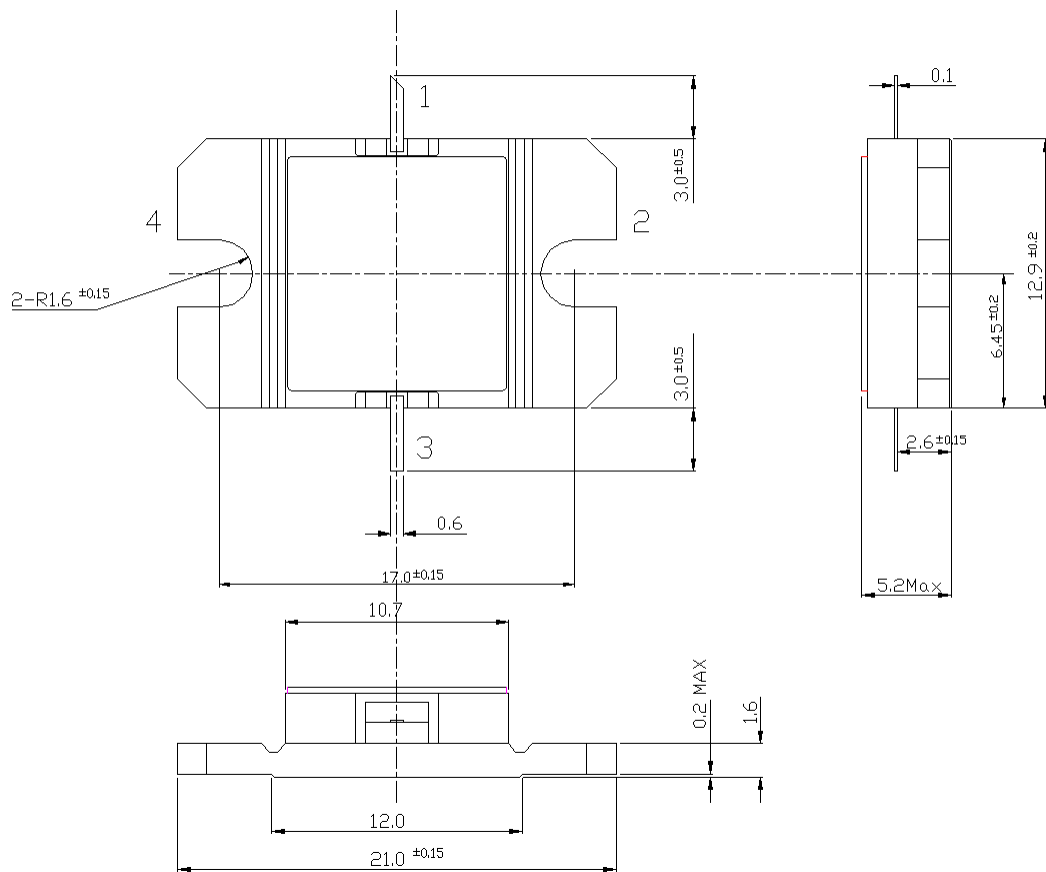


S-PARAMETERS

V_{DS} = 10V, I_{DS} = 1625mA

FREQUENCY (MHz)	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
6900	0.717	-168.0	3.148	-9.5	0.019	4.3	0.388	-134.3
7000	0.694	179.7	3.244	-21.6	0.023	-24.5	0.372	-147.0
7100	0.672	169.6	3.328	-30.4	0.026	-40.9	0.353	-156.1
7200	0.644	154.9	3.408	-43.2	0.032	-65.3	0.329	-170.0
7300	0.612	139.4	3.474	-56.4	0.037	-81.1	0.302	176.1
7400	0.583	122.2	3.507	-70.1	0.043	-99.3	0.272	160.1
7500	0.558	104.8	3.516	-83.8	0.051	-116.8	0.244	144.0
7600	0.539	87.1	3.502	-97.5	0.057	-130.9	0.215	126.1
7700	0.522	69.5	3.460	-111.3	0.063	-144.7	0.194	106.8
7800	0.509	52.6	3.398	-124.5	0.068	-158.4	0.176	86.7
7900	0.494	36.3	3.339	-137.9	0.072	-172.0	0.165	65.7
8000	0.477	20.5	3.278	-151.3	0.077	174.1	0.157	43.6

■ Package Outline
Case Style : IB



Pin Assignment

- 1 : Gate
- 2 : Source
- 3 : Drain
- 4 : Source

Unit : mm

For further information please contact:

<http://global-sei.com/Electro-optic/about/office.html>

CAUTION

This product contains **gallium arsenide (GaAs)** which can be hazardous to the human body and the environment. For safety, observe the following procedures:

- Do not put these products into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Observe government laws and company regulations when discarding this product. This product must be discarded in accordance with methods specified by applicable hazardous waste procedures.